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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/709,113	04/14/2004	Peter J. Geiss	BUR920030152US1	3112
29154	7590 10/05/2004		EXAMINER	
FREDERICK W. GIBB, III			WILSON, SCOTT R	
MCGINN & C	•		ART UNIT	PAPER NUMBER
SUITE 304	ROAD		2826	
ANNAPOLIS, MD 21401			DATE MAILED: 10/05/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

	EAK			
	Application No.	Applicant(s)		
	10/709,113	GEISS ET AL.		
Office Action Summary	Examiner	Art Unit		
	Scott R. Wilson	2826		
The MAILING DATE of this communication a Period for Reply	ppears on the cover sheet v	vith the correspondence address		
A SHORTENED STATUTORY PERIOD FOR REP THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by state Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no event, however, may a seply within the statutory minimum of the desire services of the statutory minimum of the services of	reply be timely filed irty (30) days will be considered timely. NTHS from the mailing date of this communication ABANDONED (35 U.S.C. § 133).	n.	
Status				
1) Responsive to communication(s) filed on 17	September 2004.			
2a) This action is FINAL . 2b) ⊠ Th	nis action is non-final.			
3) Since this application is in condition for allow	vance except for formal ma	tters, prosecution as to the merits is	5	
closed in accordance with the practice under	r <i>Ex parte Quayle</i> , 1935 C.	D. 11, 453 O.G. 213.		
Disposition of Claims	•			
4) Claim(s) 1-31 is/are pending in the application	on.			
4a) Of the above claim(s) 15-31 is/are withdr	awn from consideration.			
5) Claim(s) is/are allowed.				
6)⊠ Claim(s) <u>1,4-8 and 11-14</u> is/are rejected.				
7)⊠ Claim(s) <u>2,3,9 and 10</u> is/are objected to.				
8) Claim(s) are subject to restriction and	d/or election requirement.		*	
Application Papers				
9) The specification is objected to by the Exami	ner.			
10) The drawing(s) filed on 14 April 2004 is/are:	a)⊠ accepted or b) obj	ected to by the Examiner.		
Applicant may not request that any objection to the	he drawing(s) be held in abeya	ance. See 37 CFR 1.85(a).		
Replacement drawing sheet(s) including the corre			d).	
11) The oath or declaration is objected to by the	Examiner. Note the attache	ed Office Action or form PTO-152.		
Priority under 35 U.S.C. § 119				
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure	ents have been received. ents have been received in riority documents have bee	Application No		
* See the attached detailed Office action for a li	ist of the certified copies no	t received.		
Attachment(s)		· C		
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	<i>.</i> —	Summary (PTO-413) o(s)/Mail Date		
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date 4/14/04.		Informal Patent Application (PTO-152)		

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DETAILED ACTION

Election/Restrictions

Applicant's election without traverse of claims 1-14 in the response filed 17 September 2004 is acknowledged.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1 and 4-7 are rejected under 35 U.S.C. 102(b) as being anticipated by Kato. As to claim 1, Kato, Figure 11, discloses (col. 6, lines 40-60) a bipolar device comprising a base (4) and (5), an emitter (6) and (16) above said base, wherein said emitter has a T-shape with a lower section and an upper section that is wider than said lower section, spacers (13) adjacent said lower section of said emitter and beneath said upper section of said emitter, and a silicide layer (12')(col. 10, lines 30-31) adjacent said spacers and beneath said upper section of said emitter.

As to claim 4, Kato discloses (col. 7, lines 20-25) that the spacers (13) separate said emitter (16) from said silicide (12').

As to claim 5, Kato discloses that the base comprises an intrinsic base (4), and an extrinsic base (5) above said intrinsic base.

As to claim 6, Kato discloses (col. 7, lines 20-25) that the spacers (13) are insulators.

As to claim 7, Kato discloses (col. 6, lines 51-53) that layer (12), which is embodied in Figure 11 as silicide layer (12'), is formed in a self-aligned manner.

Claims 8 and 11-14 are rejected under 35 U.S.C. 102(b) as being anticipated by Kato. As to claim 8, Kato, Figure 11, discloses (col. 6, lines 40-60) a transistor device comprising a lower

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semiconductor structure (2)(col. 6, lines 31-33) having a n-type impurity, a middle semiconductor region (4) and (5) above said lower semiconductor structure, said middle semiconductor region having a p-type impurity, an upper semiconductor structure (6) and (16) above said middle semiconductor region, wherein said upper semiconductor structure has a T-shape with a lower section and an upper section that is wider than said lower section, spacers (13) adjacent said lower section of said upper semiconductor structure and beneath said upper section of said upper semiconductor structure, and a silicide layer (12') adjacent said spacers and beneath said upper section of said upper semiconductor structure.

As to claim 11, Kato discloses (col. 7, lines 20-25) that the spacers (13) separate said upper semiconductor structure from said silicide (12').

As to claim 12, Kato discloses that the middle semiconductor region comprises an intrinsic middle semiconductor region (4), and an extrinsic middle semiconductor region (5) above said intrinsic middle semiconductor region.

As to claim 13, Kato discloses (col. 7, lines 20-25) that the spacers (13) are insulators.

As to claim 14, Kato discloses (col. 6, lines 51-53) that layer (12), which is embodied in Figure 11 as silicide layer (12'), is formed in a self-aligned manner.

Allowable Subject Matter

Claims 2, 3, 9 and 10 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. No prior art discloses the claimed invention with a dielectric layer over the base and beneath the spacers with width less than the width of the base.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Scott R. Wilson whose telephone number is 571-272-1925. The examiner can normally be reached on M-F 8:30 - 4:30 Eastern.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on 571-272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

srw

September 29, 2004

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